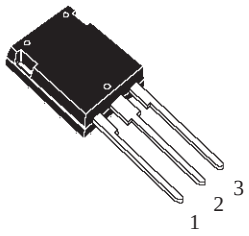
STY25NA60

N - CHANNEL 600V - 0.225Ω - 25 A - Max247
EXSTREMELY LOW GATE CHARGE POWER MOSFET

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STY25NA60	600 V	< 0.24 Ω	25 A

- TYPICAL $R_{DS(on)}$ = 0.225 Ω
- EFFICIENT AND RELIABLE MOUNTING THROUGH CLIP
- ± 30V GATE TO SOURCE VOLTAGE RATING
- 100% AVALANCHE TESTED
- LOW INTRINSIC CAPACITANCE
- GATE CHARGE MINIMIZED
- REDUCED VOLTAGE SPREAD

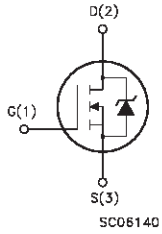


Max247™

DESCRIPTION

The Max247™ package is a new high volume power package exibiting the same footprint as the industry standard TO-247, but designed to accomodate much larger silicon chips, normally supplied in bigger packages such as TO-264.The increased die capacity makes the device idealto reduce component count in multiple paralleled designs and save board space with respect to larger packages.

INTERNAL SCHEMATIC DIAGRAM



APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLY (SMPS)
- DC-AC CONVERTER FOR WELDING EQUIPMENT AND UNINTERRUPTABLE POWER SUPPLY AND MOTOR DRIVE

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source Voltage (V_{GS} = 0)	600	V
V_{DGR}	Drain- gate Voltage (R_{GS} = 20 kΩ)	600	V
V_{GS}	Gate-source Voltage	± 30	V
I_D	Drain Current (continuous) at T_c = 25 °C	25	A
I_D	Drain Current (continuous) at T_c = 100 °C	16.5	A
I_{DM}(•)	Drain Current (pulsed)	100	A
P_{tot}	Total Dissipation at T_c = 25 °C	300	W
	Derating Factor	2.4	W/°C
T_{stg}	Storage Temperature	-55 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

(•) Pulse width limited by safe operating area

THERMAL DATA

$R_{thj\text{-}case}$	Thermal Resistance Junction-case	Max	0.42	°C/W
$R_{thj\text{-}amb}$	Thermal Resistance Junction-ambient	Max	40	°C/W
$R_{thc\text{-}sink}$	Thermal Resistance Case-Heatsink with Conductive Grease	Typ	0.05	°C/W

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	25	A
E_{AS}	Single Pulse Avalanche Energy (starting T_j = 25 °C, $I_D = I_{AR}$, V_{DD} = 50 V)	3000	mJ

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	I_D = 250 µA V_{GS} = 0	600			V
I_{DSS}	Zero Gate Voltage Drain Current (V_{GS} = 0)	V_{DS} = Max Rating V_{DS} = Max Rating T_c = 125 °C			50 500	µA µA
I_{GSS}	Gate-body Leakage Current (V_{DS} = 0)	V_{GS} = ± 30 V			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS} I_D = 250 µA	3	4	5	V
$R_{DS(on)}$	Static Drain-source On Resistance	V_{GS} = 10 V I_D = 12.5 A		0.225	0.24	Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ V_{GS} = 10 V	25			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (*)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ I_D = 12.5 A	20			S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V_{DS} = 25 V f = 1 MHz V_{GS} = 0		6200 690 195		pF pF pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay Time Rise Time	V_{DD} = 300 V I_D = 12.5 A R_G = 4.7 Ω V_{GS} = 10 V (see test circuit, figure 3)		45 70		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD} = 480 V I_D = 25 A V_{GS} = 10 V		240 25 115	315	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	V_{DD} = 480 V I_D = 25 A R_G = 4.7 Ω V_{GS} = 10 V (see test circuit, figure 5)		70 25 105		ns ns ns

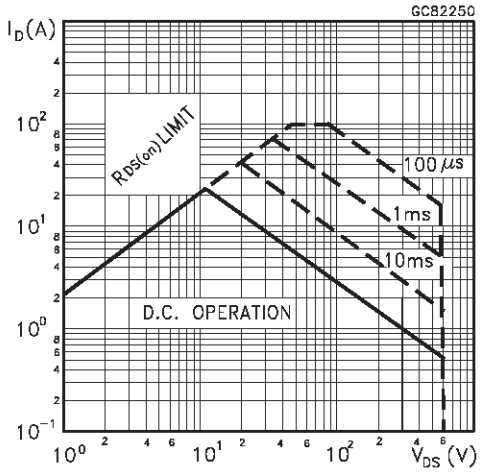
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM}(•)	Source-drain Current Source-drain Current (pulsed)				25 100	A A
V_{SD} (*)	Forward On Voltage	I_{SD} = 25 A V_{GS} = 0			2	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 25 A di/dt = 100 A/µs V_{DD} = 100 V T_j = 150 °C (see test circuit, figure 5)		840 19.5 46.5		ns µC A

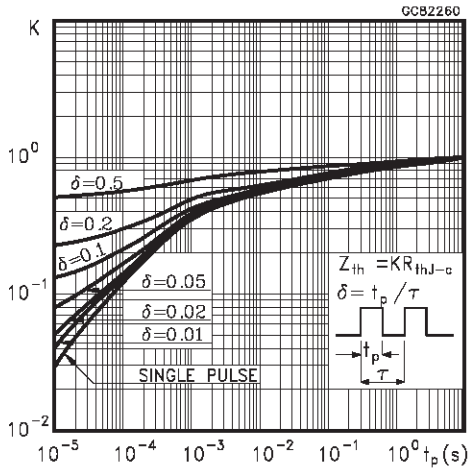
(*) Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %

(•) Pulse width limited by safe operating area

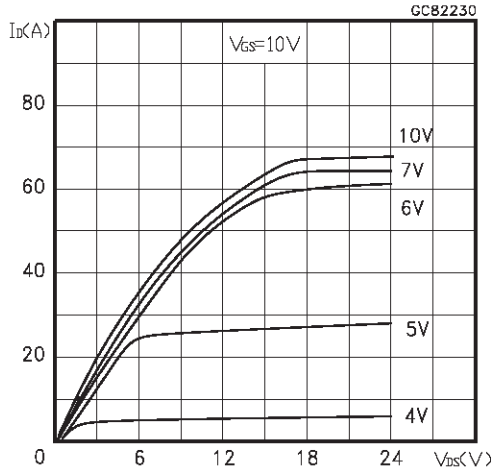
Safe Operating Area



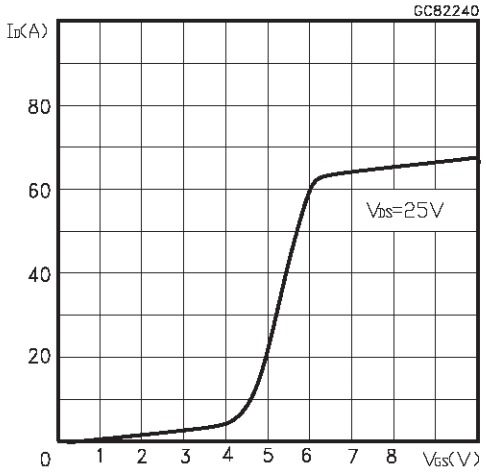
Thermal Impedance



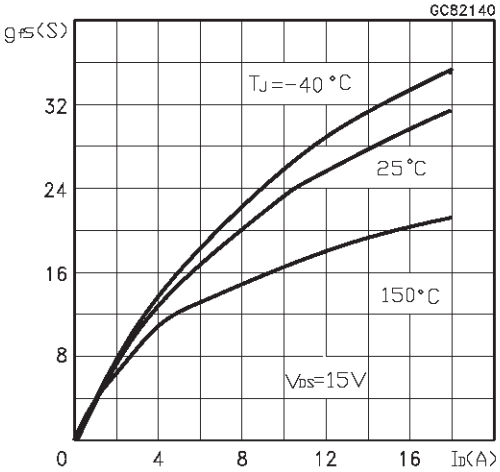
Output Characteristics



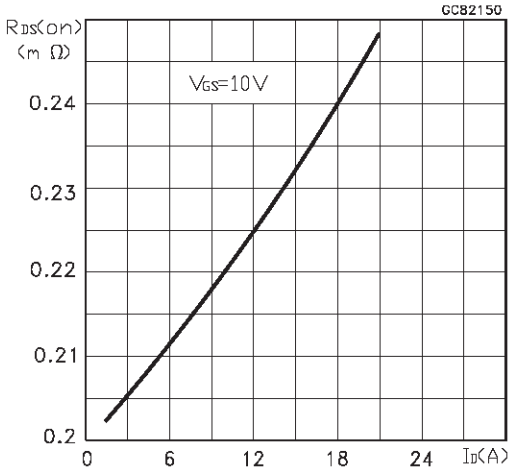
Transfer Characteristics



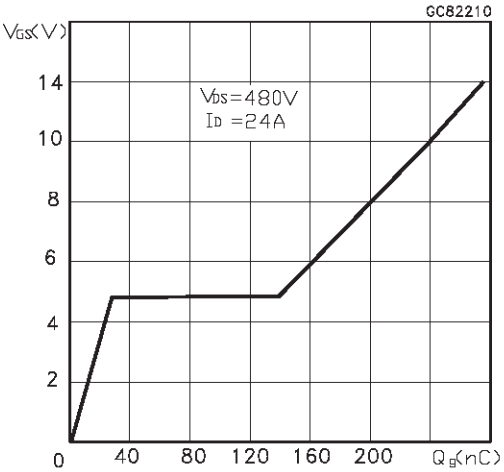
Transconductance



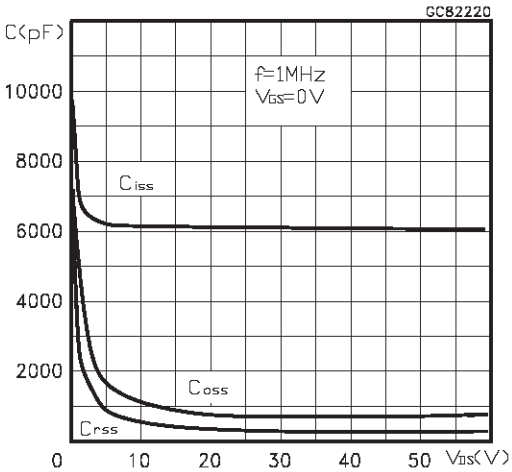
Static Drain-source On Resistance



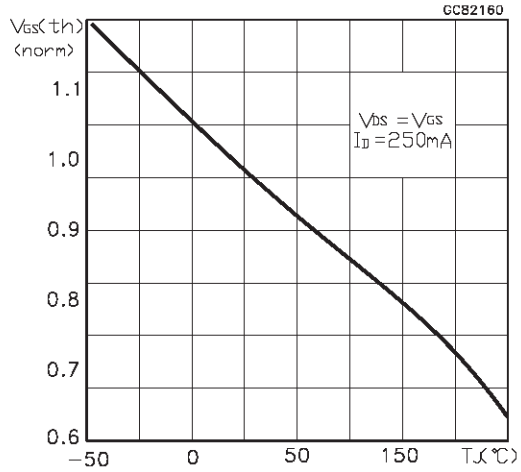
Gate Charge vs Gate-source Voltage



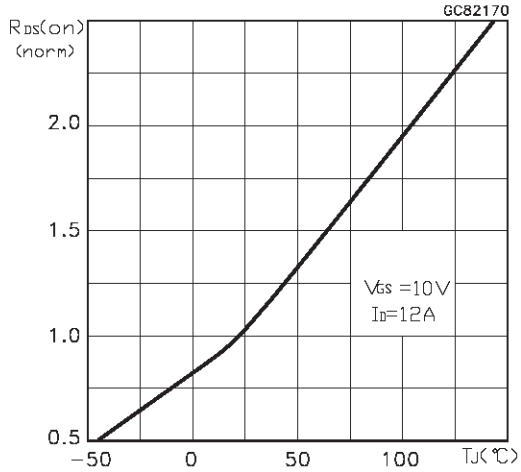
Capacitance Variations



Normalized Gate Threshold Voltage vs Temperature



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

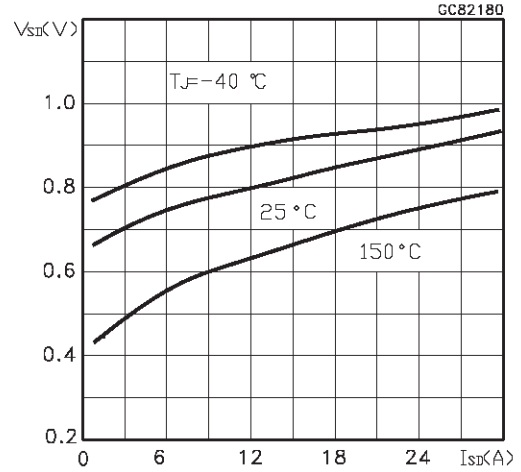


Fig. 1: Unclamped Inductive Load Test Circuit

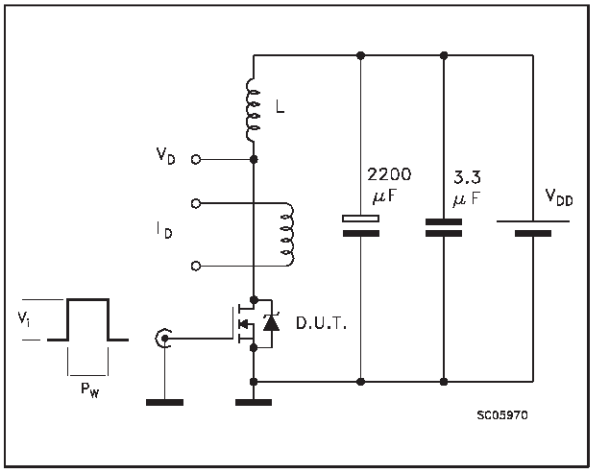


Fig. 2: Unclamped Inductive Waveform

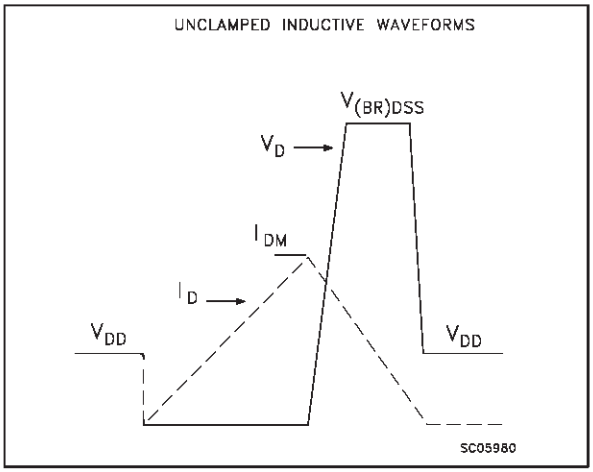


Fig. 3: Switching Times Test Circuits For Resistive Load

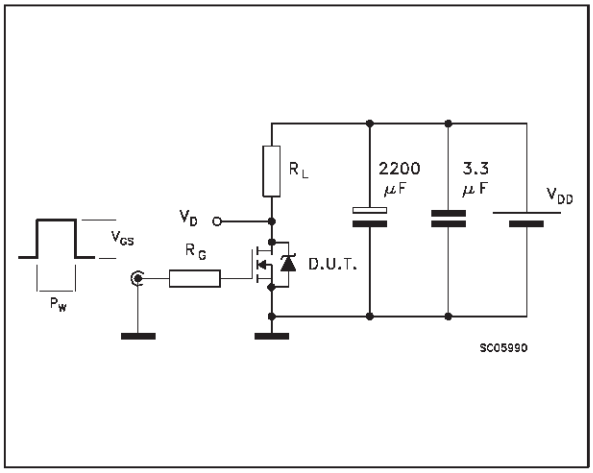


Fig. 4: Gate Charge test Circuit

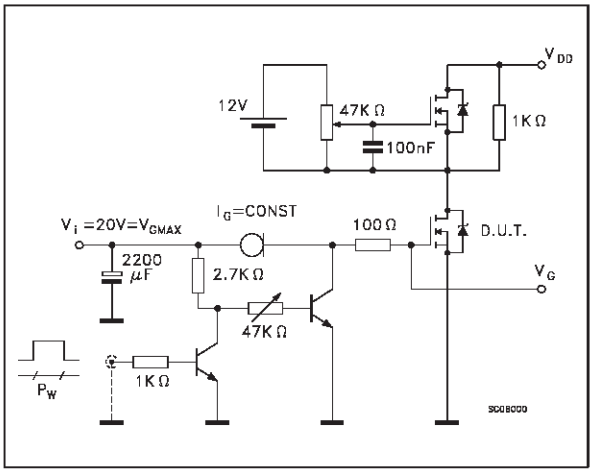
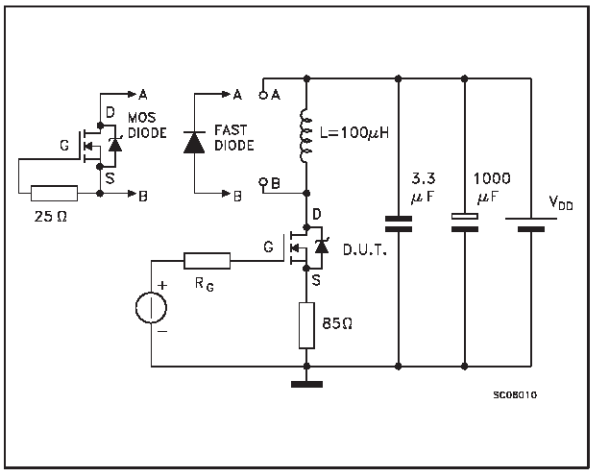
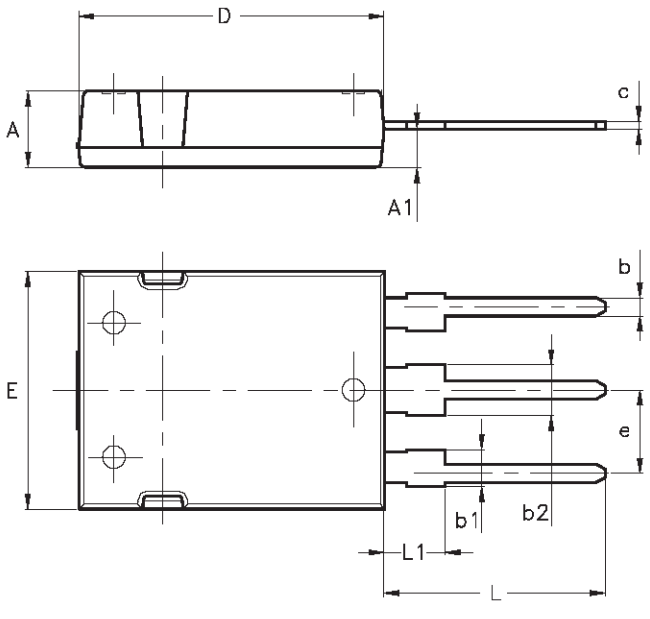


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



Max247 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.70		5.30			
A1	2.20		2.60			
b	1.00		1.40			
b1	2.00		2.40			
b2	3.00		3.40			
c	0.40		0.80			
D	19.70		20.30			
e	5.35		5.55			
E	15.30		15.90			
L	14.20		15.20			
L1	3.70		4.30			



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